

General purpose transistor (isolated transistor and diode)

US5L10

A 2SD2674 and a RB461F are housed independently in a TUMT5 package.

●Applications

DC / DC converter
Motor driver

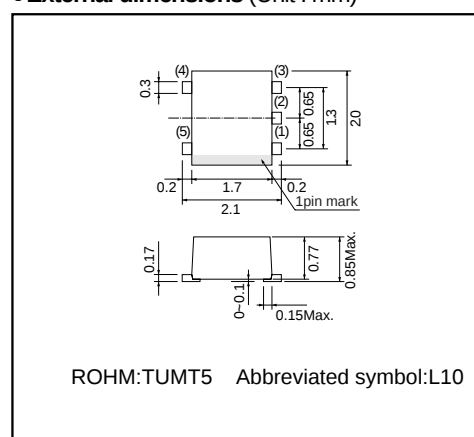
●Features

- 1) Tr : Low $V_{CE(sat)}$
Di : Low V_F
- 2) Small package

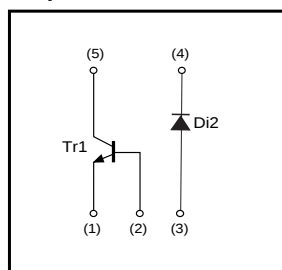
●Structure

Silicon epitaxial planar transistor
Schottky barrier diode

●External dimensions (Unit : mm)



●Equivalent circuit



●Packaging specification s

Type	US5L10
Package	TUMT5
Marking	L10
Code	TR
Basic ordering unit(pieces)	3000

Transistors

●Absolute maximum ratings (Ta=25°C)

Tr1

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	15	V
Collector-emitter voltage	V _{CEO}	12	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	I _C	1.5	A
	I _{CP}	3	A *1
Power dissipation	P _C	0.9	W/ELEMENT *2
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	−40 to +125	°C

*1 Single pulse, P_w=1ms.

*2 Mounted on a 25mm×25mm×10.8mm ceramic substrate

Di2

Parameter	Symbol	Limits	Unit
Average rectified forward current	I _F	700	mA
Forward current surge peak (60Hz, 1∞)	I _{FSM}	3	A
Reverse voltage (DC)	V _R	20	V
Junction temperature	T _j	125	°C
Range of storage temperature	T _{stg}	−40 to +125	°C
Peak reverse voltage	V _{RM}	25	V
Power dissipation	P _D	0.5	W/ELEMENT *

* Mounted on a 25mm×25mm×10.8mm ceramic substrate

Tr1& Di2

Parameter	Symbol	Limits	Unit
Total power dissipation	P _D	0.4	W/TOTAL *1
		1.0	W/TOTAL *2

*1 Each terminal mounted on a recommended land

*2 Mounted on a 25mm×25mm×10.8mm ceramic substrate

●Electrical characteristics (Ta=25°C)

Tr1

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	15	–	–	V	I _C =10μA
Collector-emitter breakdown voltage	BV _{CEO}	12	–	–	V	I _C =1mA
Emitter-base breakdown voltage	BV _{EBO}	6	–	–	V	I _E =10μA
Collector cutoff current	I _{CBO}	–	–	100	nA	V _{CB} =15V
Emitter cutoff current	I _{EBO}	–	–	100	nA	V _{EB} =6V
Collector-emitter saturation voltage	V _{CE(sat)}	–	85	200	mV	I _C /I _B =500mA/25mA
DC current gain	h _{FE}	270	–	680	–	V _{CE} /I _C =2V/200mA *
Transition frequency	f _T	–	400	–	MHz	V _{CE} =2V, I _E =−200mA, f=100MHz *
Collector output capacitance	C _{ob}	–	12	–	pF	V _{CB} =10V, I _E =0A, f=1MHz

* Pulsed

Di2

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _F	–	450	490	mV	I _F =700mA
Reverse current	I _R	–	–	200	μA	V _R =20V
Reverse recovery time	t _{rr}	–	9	–	ns	I _F =I _R =100mA, I _{rr} =0.1I _R

Transistors

●Electrical characteristic curves

Tr1

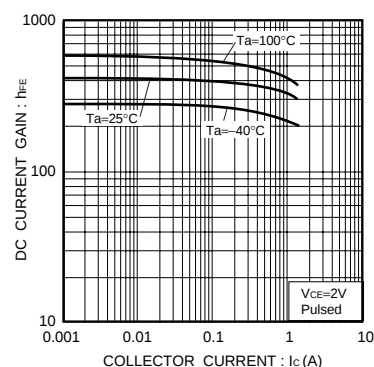
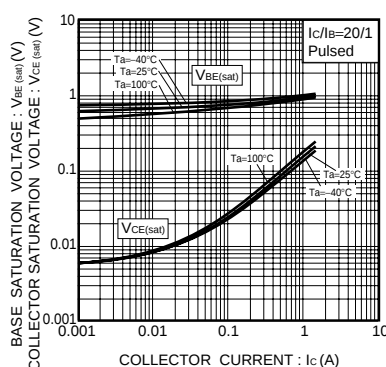
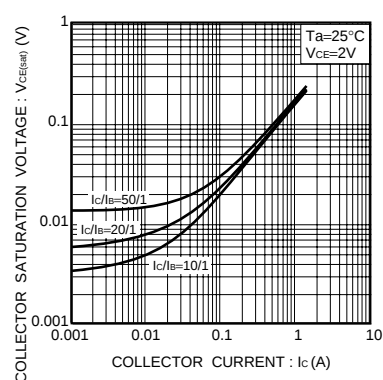
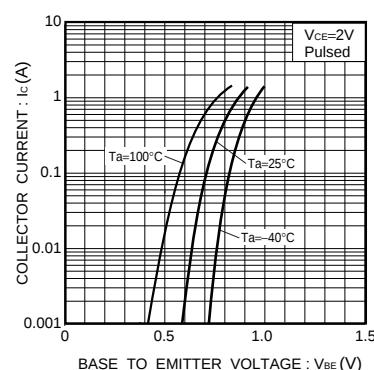
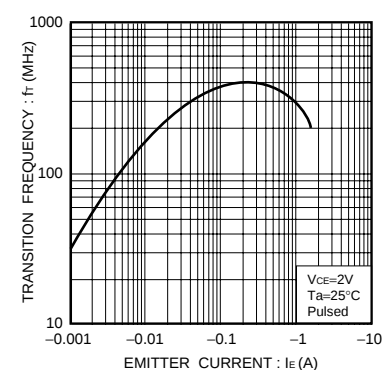
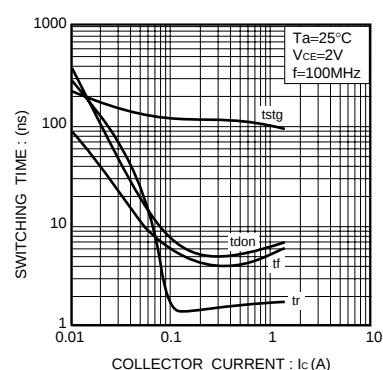
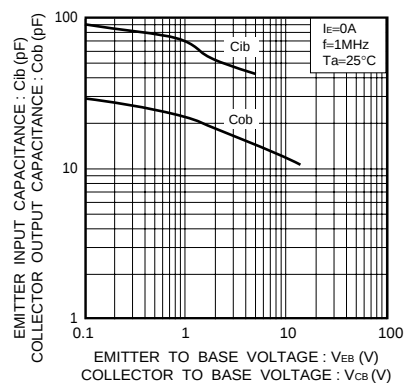
Fig.1 DC current gain
vs. collector currentFig.2 Collector-emitter saturation voltage
base-emitter saturation voltage
vs. collector currentFig.3 Collector-emitter saturation voltage
vs. collector currentFig.4 Grounded emitter propagation
characteristicsFig.5 Gain bandwidth product
vs. emitter current

Fig.6 Switching time

Fig.7 Collector output capacitance
vs. collector-base voltage
Emitter input capacitance
vs. emitter-base voltage

Transistors

Di2

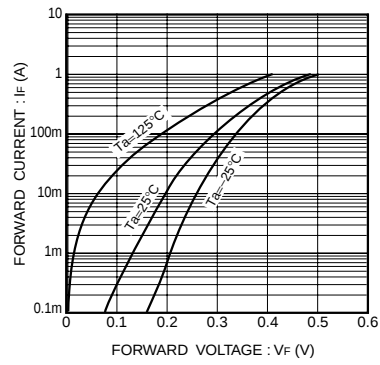


Fig.9 Forward characteristics

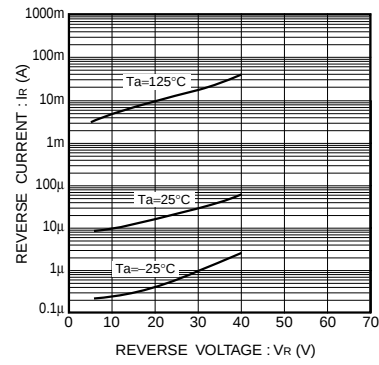


Fig.10 Reverse characteristics

Notes

- No technical content pages of this document may be reproduced in any form or transmitted by any means without prior permission of ROHM CO.,LTD.
- The contents described herein are subject to change without notice. The specifications for the product described in this document are for reference only. Upon actual use, therefore, please request that specifications to be separately delivered.
- Application circuit diagrams and circuit constants contained herein are shown as examples of standard use and operation. Please pay careful attention to the peripheral conditions when designing circuits and deciding upon circuit constants in the set.
- Any data, including, but not limited to application circuit diagrams information, described herein are intended only as illustrations of such devices and not as the specifications for such devices. ROHM CO.,LTD. disclaims any warranty that any use of such devices shall be free from infringement of any third party's intellectual property rights or other proprietary rights, and further, assumes no liability of whatsoever nature in the event of any such infringement, or arising from or connected with or related to the use of such devices.
- Upon the sale of any such devices, other than for buyer's right to use such devices itself, resell or otherwise dispose of the same, no express or implied right or license to practice or commercially exploit any intellectual property rights or other proprietary rights owned or controlled by
- ROHM CO., LTD. is granted to any such buyer.
- Products listed in this document are no antiradiation design.

The products listed in this document are designed to be used with ordinary electronic equipment or devices (such as audio visual equipment, office-automation equipment, communications devices, electrical appliances and electronic toys).

Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

About Export Control Order in Japan

Products described herein are the objects of controlled goods in Annex 1 (Item 16) of Export Trade Control Order in Japan.

In case of export from Japan, please confirm if it applies to "objective" criteria or an "informed" (by MITI clause) on the basis of "catch all controls for Non-Proliferation of Weapons of Mass Destruction.